



PMPB15XN

20 V, single N-channel Trench MOSFET

13 September 2012

Product data sheet

1. Product profile

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Trench MOSFET technology
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Exposed drain pad for excellent thermal conduction
- Tin-plated 100 % solderable side pads for optical solder inspection

1.3 Applications

- Charging switch for portable devices
- DC-to-DC converters
- Power management in battery-driven portable devices
- Hard disk and computing power management

1.4 Quick reference data

Table 1. Quick reference data

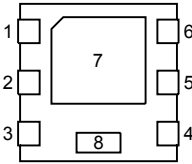
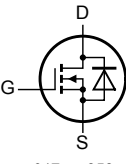
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_J = 25\text{ }^{\circ}\text{C}$		-	-	20	V
V_{GS}	gate-source voltage			-12	-	12	V
I_D	drain current	$V_{GS} = 4.5\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}; t \leq 5\text{ s}$	[1]	-	-	10.4	A
Static characteristics							
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}; I_D = 7.3\text{ A}; T_J = 25\text{ }^{\circ}\text{C}$		-	18	21	m Ω

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

nexperia

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	 Transparent top view DFN2020MD-6 (SOT1220)	 017aaa253
2	D	drain		
3	G	gate		
4	S	source		
5	D	drain		
6	D	drain		
7	D	drain		
8	S	source		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMPB15XN	DFN2020MD-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220

4. Marking

Table 4. Marking codes

Type number	Marking code
PMPB15XN	1J

5. Limiting values

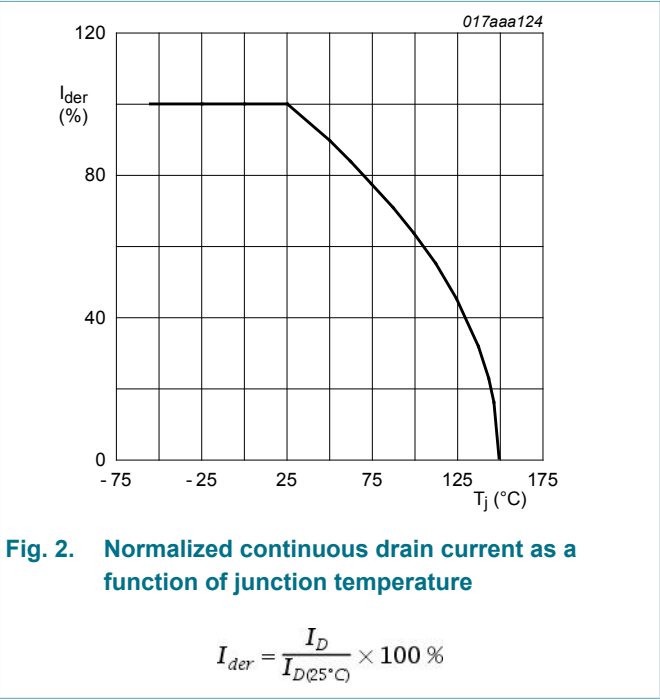
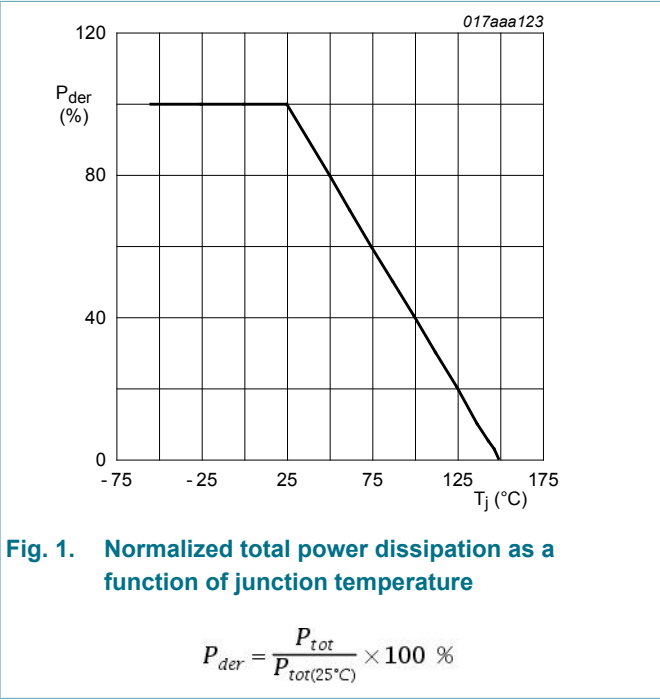
Table 5. Limiting values

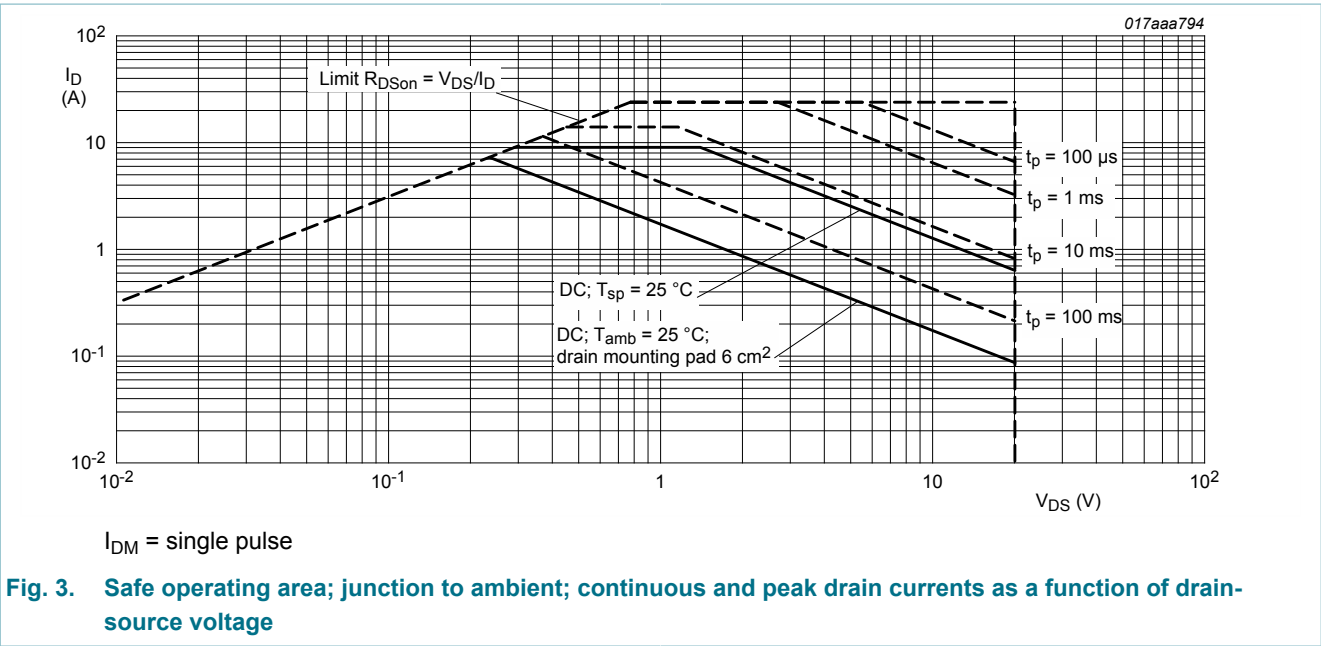
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	$T_j = 25\text{ }^{\circ}\text{C}$		-	20	V
V_{GS}	gate-source voltage			-12	12	V
I_D	drain current	$V_{GS} = 4.5\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}; t \leq 5\text{ s}$	[1]	-	10.4	A
		$V_{GS} = 4.5\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}$	[1]	-	7.3	A
		$V_{GS} = 4.5\text{ V}; T_{amb} = 100\text{ }^{\circ}\text{C}$	[1]	-	4.6	A
I_{DM}	peak drain current	$T_{amb} = 25\text{ }^{\circ}\text{C}; \text{single pulse}; t_p \leq 10\text{ }\mu\text{s}$		-	24	A
P_{tot}	total power dissipation	$T_{amb} = 25\text{ }^{\circ}\text{C}$	[1]	-	1.7	W

Symbol	Parameter	Conditions		Min	Max	Unit
		T _{amb} = 25 °C; t ≤ 5 s	[1]	-	3.5	W
		T _{sp} = 25 °C		-	12.5	W
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain diode						
I _S	source current	T _{amb} = 25 °C	[1]	-	2	A

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



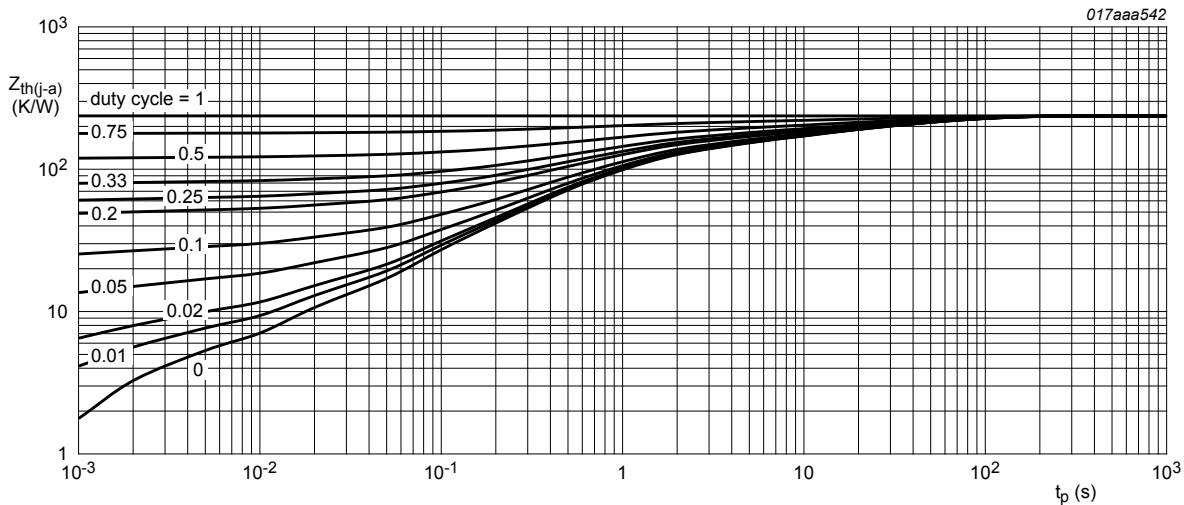


6. Thermal characteristics

Table 6. Thermal characteristics

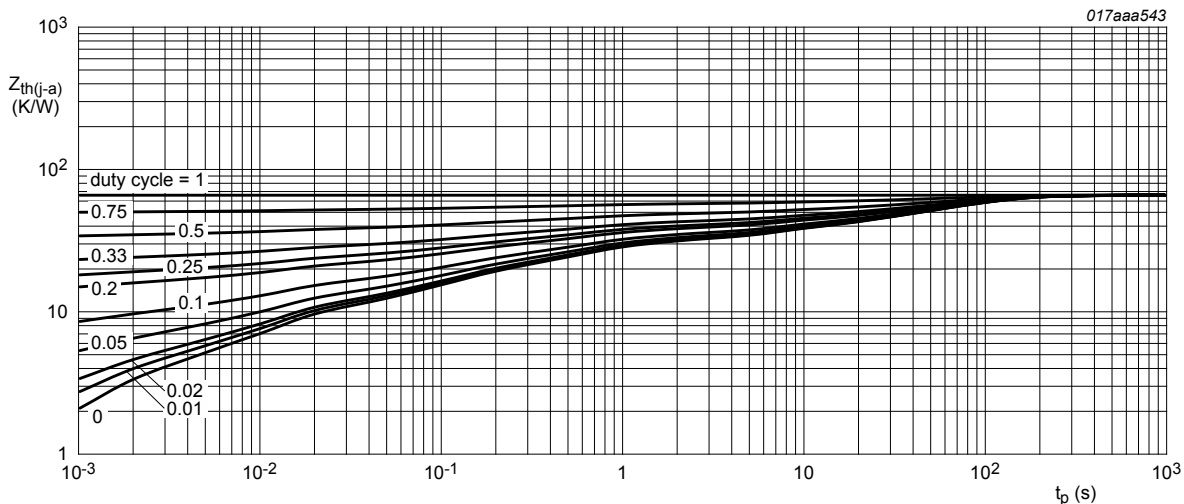
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	235	270	K/W
			[2]	-	67	74	K/W
		in free air; $t \leq 5$ s	[2]	-	33	36	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	5	10	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 6 cm²

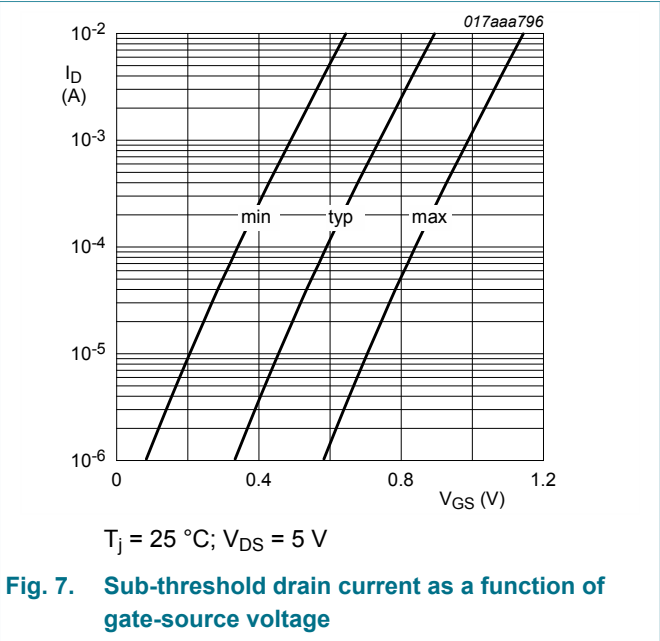
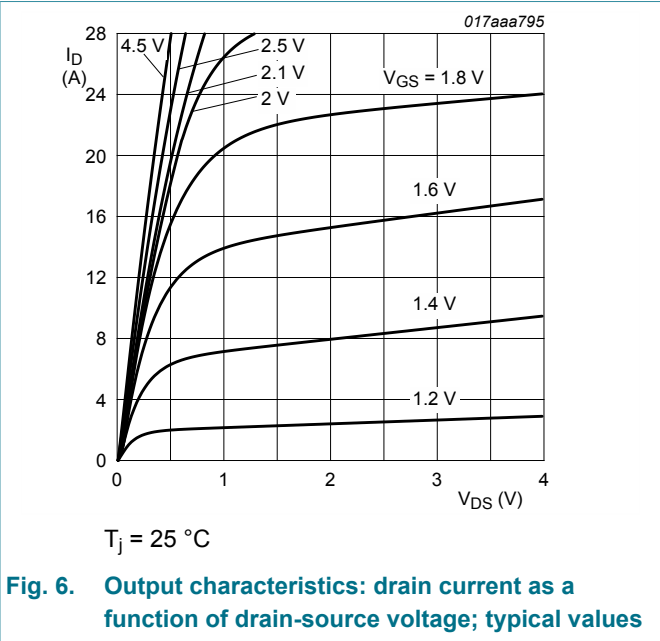
Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250\text{ }\mu\text{A}$; $V_{GS} = 0\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$	20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250\text{ }\mu\text{A}$; $V_{DS} = V_{GS}$; $T_j = 25\text{ }^\circ\text{C}$	0.4	0.65	0.9	V
I_{DSS}	drain leakage current	$V_{DS} = 20\text{ V}$; $V_{GS} = 0\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$	-	-	1	μA
I_{GSS}	gate leakage current	$V_{GS} = -12\text{ V}$; $V_{DS} = 0\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$	-	-	-100	nA

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
R _{DSon}	drain-source on-state resistance	V _{GS} = 12 V; V _{DS} = 0 V; T _j = 25 °C		-	-	100	nA
		V _{GS} = 4.5 V; I _D = 7.3 A; T _j = 25 °C		-	18	21	mΩ
		V _{GS} = 4.5 V; I _D = 7.3 A; T _j = 150 °C		-	27	32	mΩ
		V _{GS} = 2.5 V; I _D = 6.4 A; T _j = 25 °C		-	21	27	mΩ
		V _{GS} = 1.8 V; I _D = 2.1 A; T _j = 25 °C		-	23	41	mΩ
g _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 7.3 A; T _j = 25 °C		-	30	-	S
R _G	gate resistance	f = 1 MHz		-	2	-	Ω
Dynamic characteristics							
Q _{G(tot)}	total gate charge	V _{DS} = 10 V; I _D = 7.3 A; V _{GS} = 4.5 V; T _j = 25 °C		-	13.4	20.2	nC
Q _{GS}	gate-source charge			-	1.5	-	nC
Q _{GD}	gate-drain charge			-	2.6	-	nC
C _{iss}	input capacitance	V _{DS} = 10 V; f = 1 MHz; V _{GS} = 0 V; T _j = 25 °C		-	1240	-	pF
C _{oss}	output capacitance			-	145	-	pF
C _{rss}	reverse transfer capacitance			-	125	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 10 V; I _D = 7.3 A; V _{GS} = 4.5 V; R _{G(ext)} = 6 Ω; T _j = 25 °C		-	9	-	ns
t _r	rise time			-	24	-	ns
t _{d(off)}	turn-off delay time			-	31	-	ns
t _f	fall time			-	36	-	ns
Source-drain diode							
V _{SD}	source-drain voltage	I _S = 2 A; V _{GS} = 0 V; T _j = 25 °C		-	0.7	1.2	V



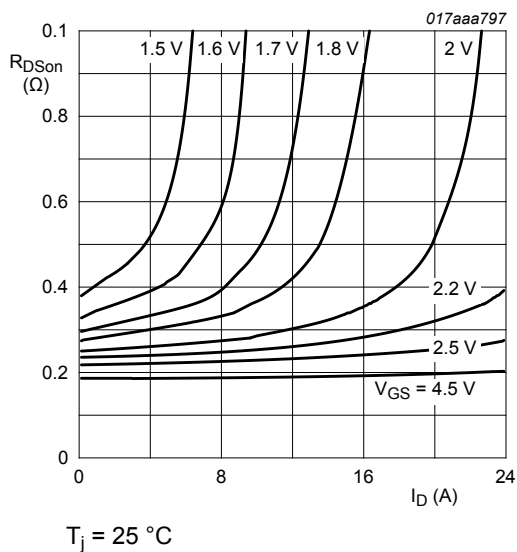


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

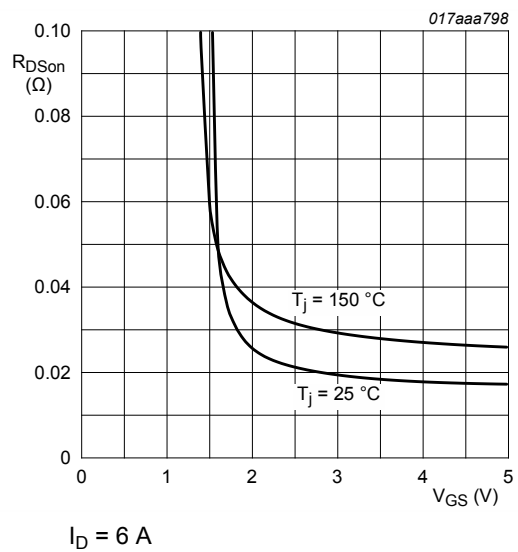


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

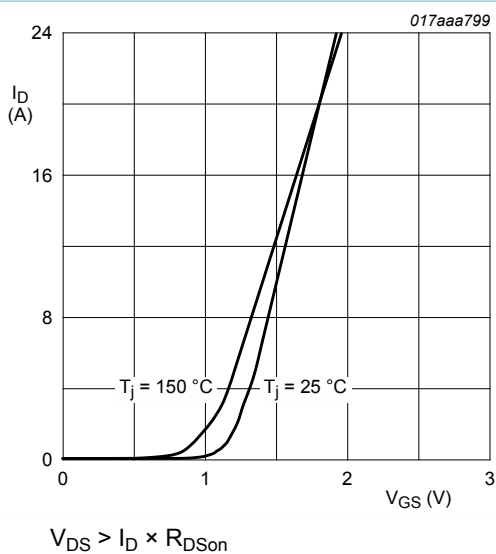


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

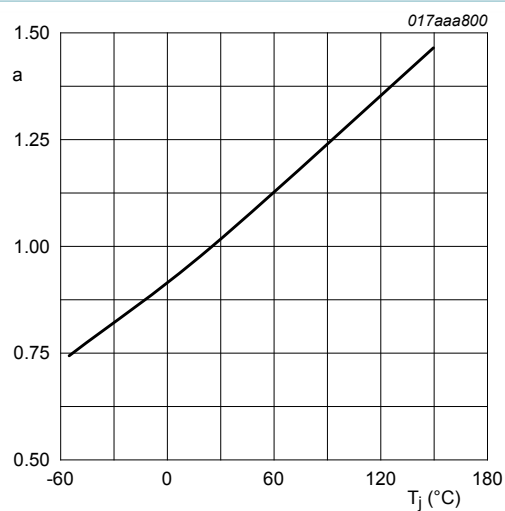


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon}(25^\circ\text{C})}$$

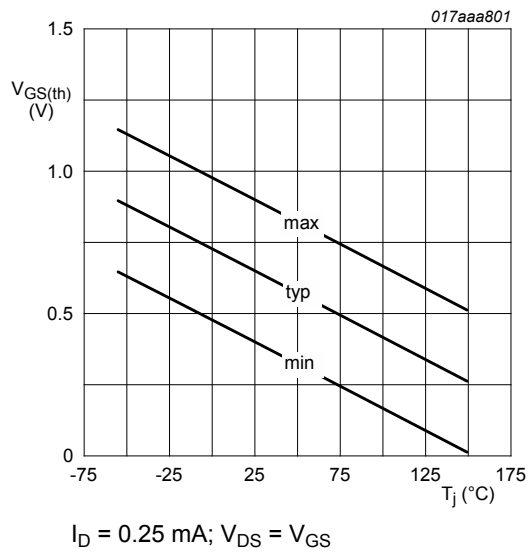


Fig. 12. Gate-source threshold voltage as a function of junction temperature

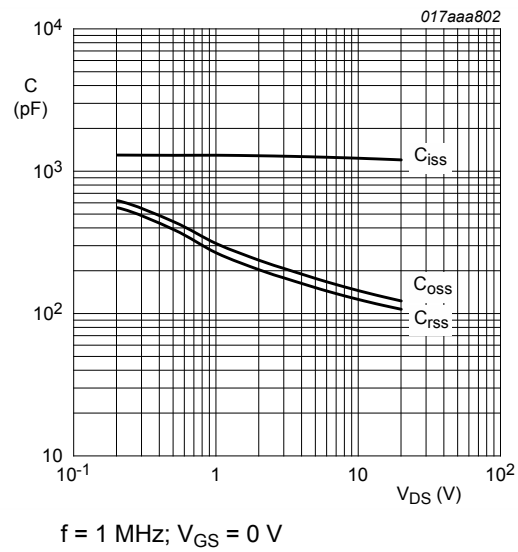


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

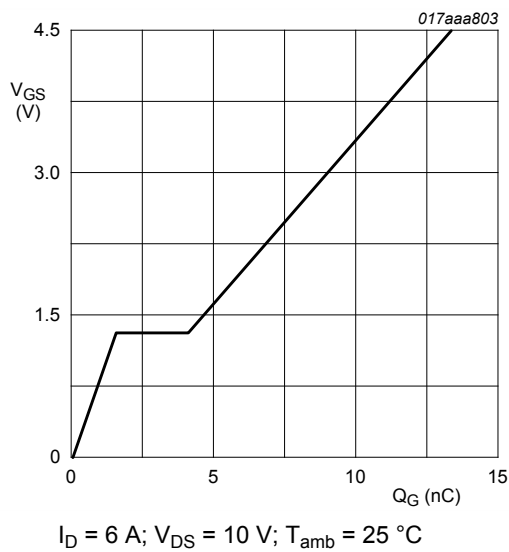


Fig. 14. Gate-source voltage as a function of gate charge; typical values

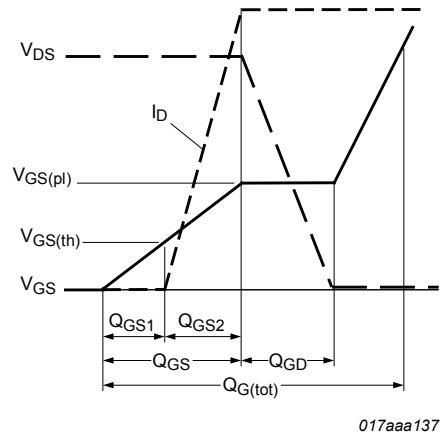
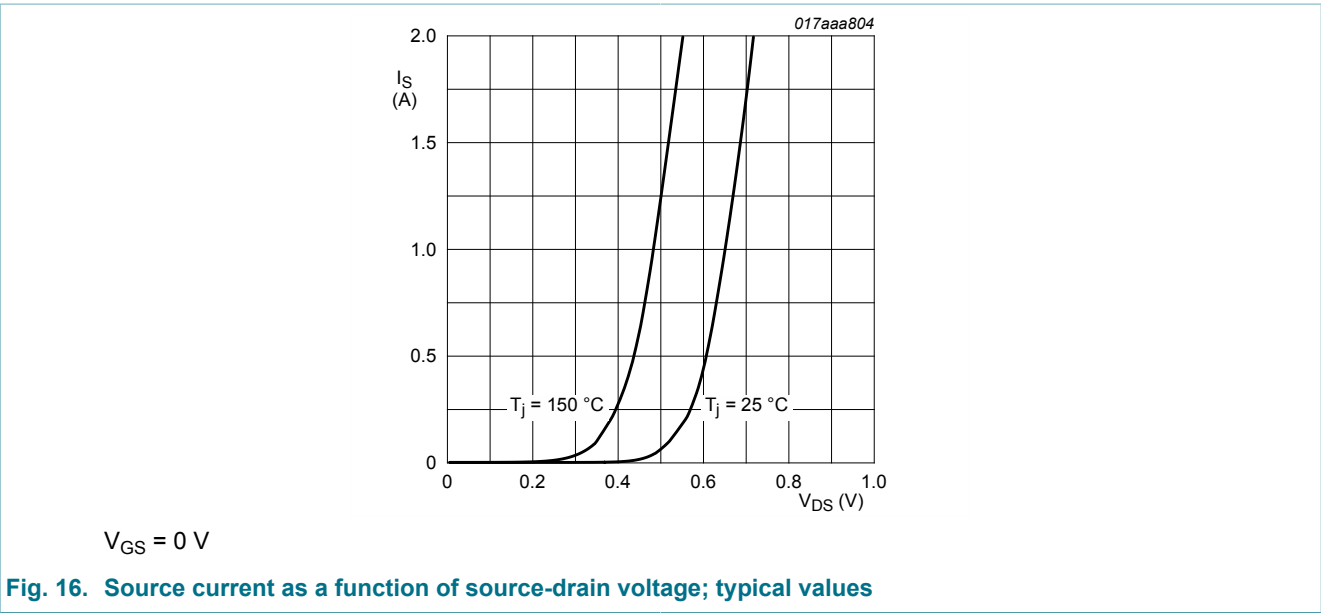
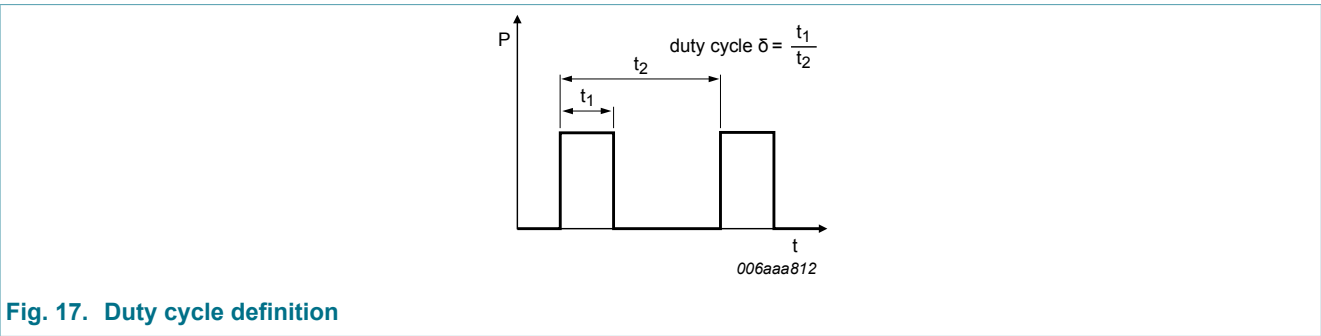


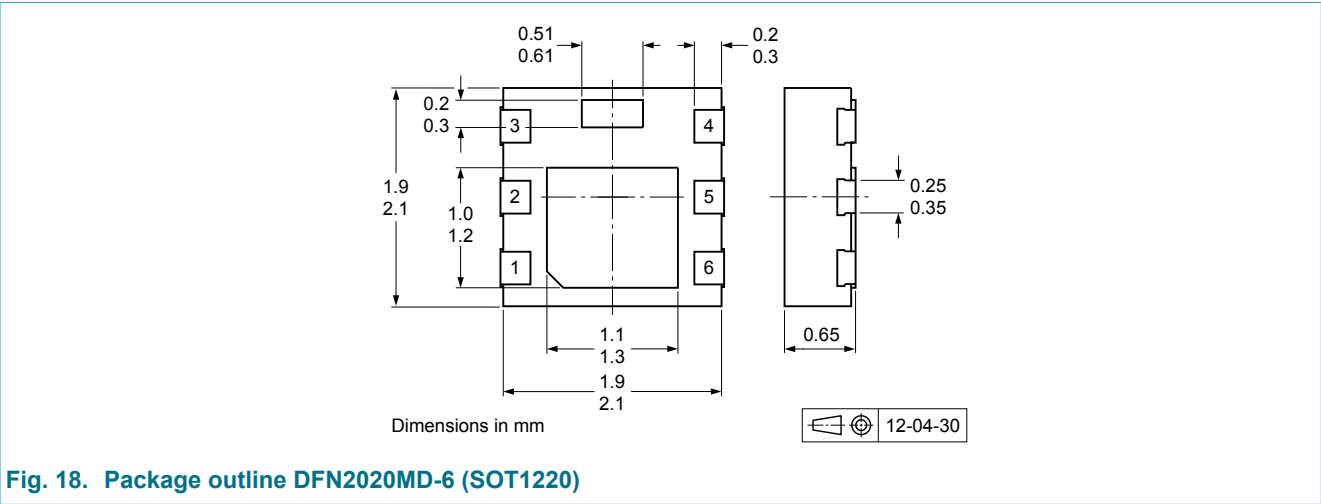
Fig. 15. Gate charge waveform definitions



8. Test information



9. Package outline



10. Soldering

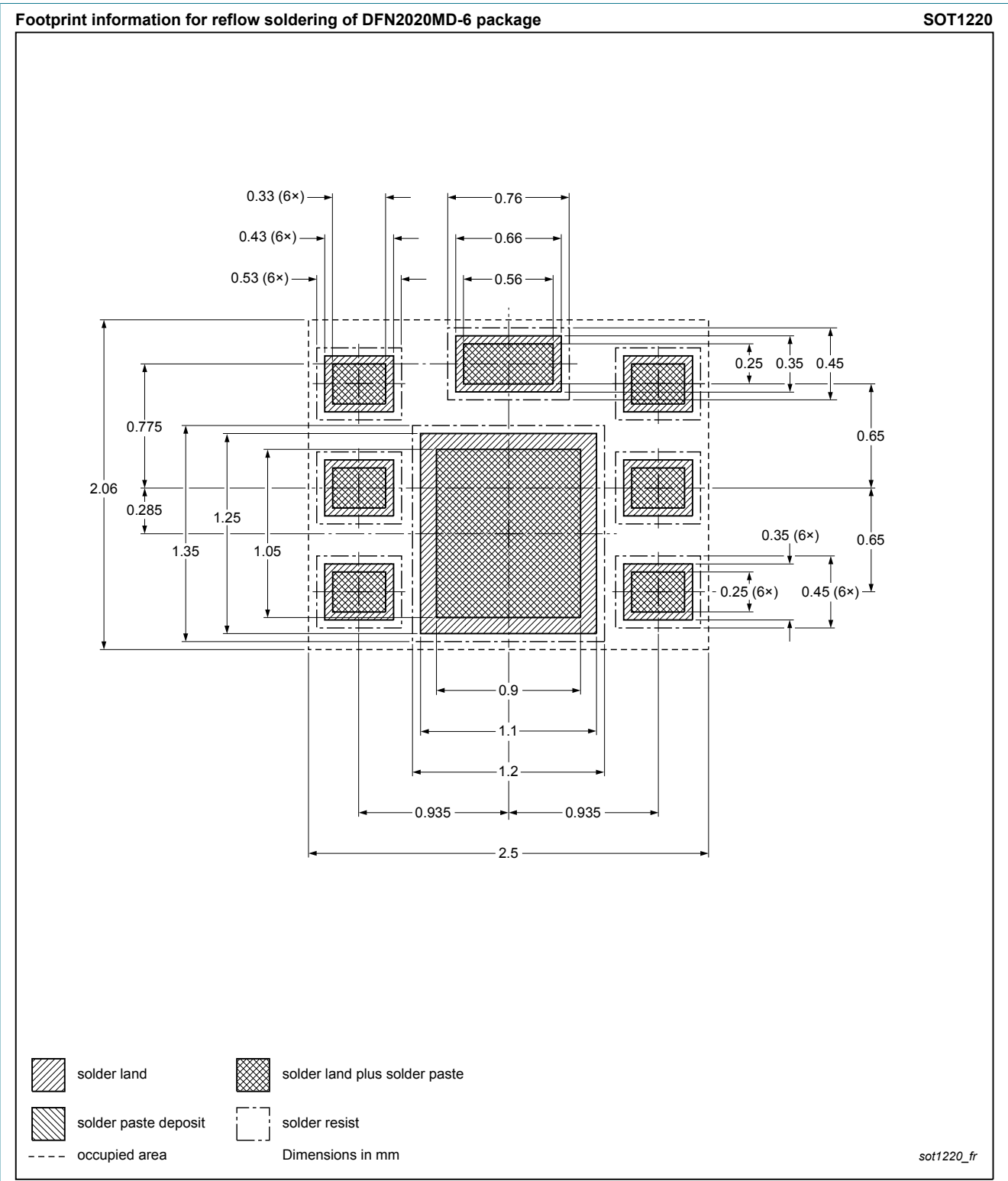


Fig. 19. Reflow soldering footprint for DFN2020MD-6 (SOT1220)

11. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMPB15XN v.1	20120913	Product data sheet	-	-

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